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December 2012

## FDS6699S 30V N-Channel PowerTrench<sup>®</sup> SyncFET<sup>™</sup>

## Features

- 21 A, 30 V Max  $R_{DS(ON)} = 3.6 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$ Max  $R_{DS(ON)} = 4.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Includes SyncFET Schottky body diode
- High performance trench technology for extremely low R<sub>DS(ON)</sub> and fast switching
- High power and current handling capability
- 100% R<sub>G</sub> (Gate Resistance) tested

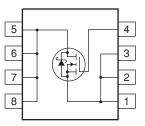
## **Applications**

- Synchronous Rectifier for DC/DC Converters -
  - Notebook Vcore low side switch
  - Point of Load low side switch

## **General Description**

The FDS6699S is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDS6699S includes an integrated Schottky diode using Fair-child's monolithic SyncFET technology.





## Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current – Continuous	(Note 1a)	21	A
	– Pulsed		105	
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 4)	541	mJ
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	_
		(Note 1c)	1	_
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C
Thermal Cha	aracteristics	1		-
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	1

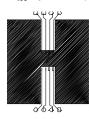
## Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6699S	FDS6699S	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Charact	teristics	L		1		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 1 mA$	30			V
$\frac{\Delta BV_{\text{DSS}}}{\Delta T_{\text{J}}}$	Breakdown Voltage Temperature Coefficient	$I_D = 1$ mA, Referenced to 25°C		28		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			500	μA
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Charact	teristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1 \text{ mA}$	1	1.4	3	V
$\frac{\Delta V_{\text{GS(th)}}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1$ mA, Referenced to 25°C		-3.2		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance			3.0 3.6 4.6	3.6 4.5 5.6	mΩ
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 21 A		100		S
Dynamic C	haracteristics		•			
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		3610	4800	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		1080	1435	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			340	680	pF
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 15 mV, f = 1.0 MHz	0.4	1.8	3.1	Ω
Switching (	Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn–On Delay Time	$V_{DD} = 15 \text{ V}, \text{ I}_{D} = 1 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		11	20	ns
t <sub>r</sub>	Turn–On Rise Time			12	22	ns
t <sub>d(off)</sub>	Turn–Off Delay Time			73	117	ns
t <sub>f</sub>	Turn–Off Fall Time			38	61	ns
Q <sub>g(TOT)</sub>	Total Gate Charge at Vgs = 10V	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 21 A,		65	91	nC
Qg	Total Gate Charge at Vgs = 5V			35	49	nC
Q <sub>gs</sub>	Gate-Source Charge			9		nC
Q <sub>gd</sub>	Gate-Drain Charge			11		nC
Drain-Sour	ce Diode Characteristics and Maximun	n Ratings				
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 3.5 \text{ A}$ (Note 2)		0.36	0.7	V
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 21 A,		32		ns
I <sub>RM</sub>	Diode Reverse Recovery Current	$d_{iF}/d_t = 300 \text{ A}/\mu \text{s} \qquad (\text{Note 3})$		2.2		Α
Q <sub>rr</sub>	Diode Reverse Recovery Charge			35		nC

#### Notes:

1. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}^{\text{out}}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



 a) 50°/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b) 105°/W when mounted on a .04 in<sup>2</sup> pad of 2 oz copper

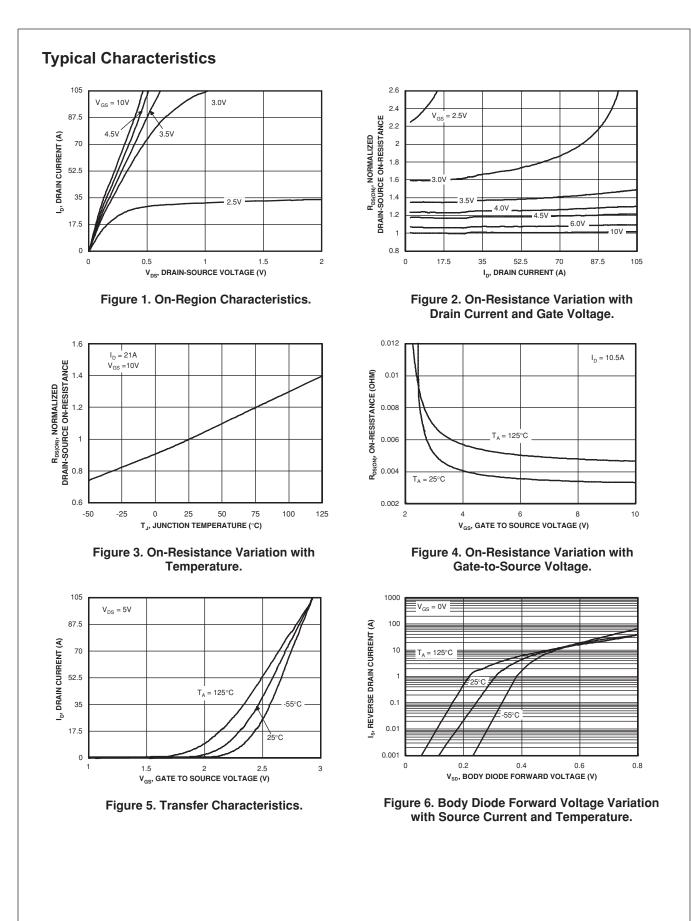
c) 125°/W when mounted on a minimum pad.

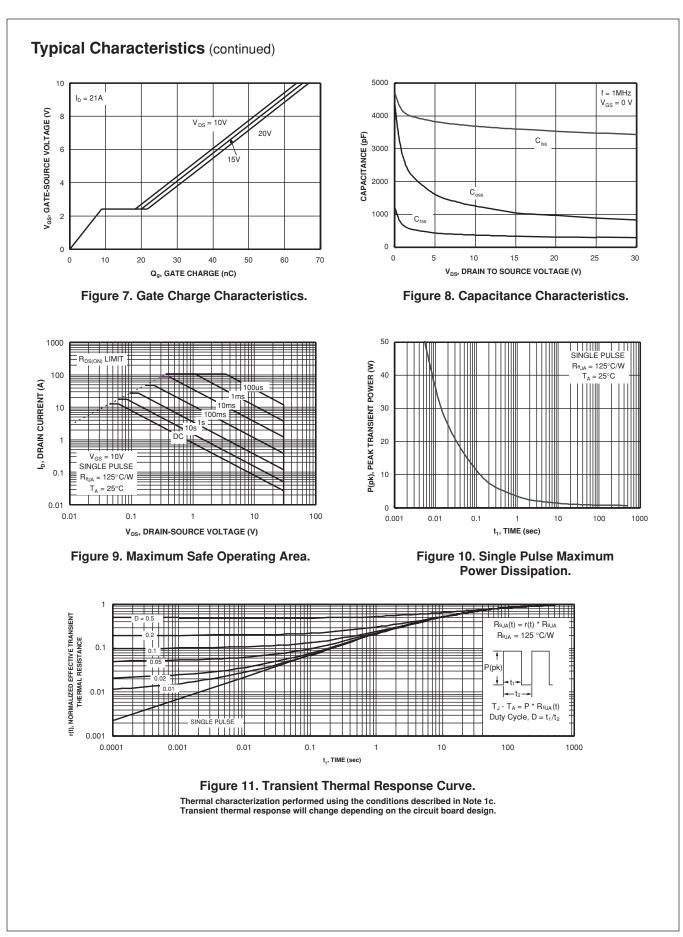
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Scale 1 : 1 on letter size paper

- 2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%
- $\label{eq:second} \textbf{3. See "SyncFET Schottky body diode characteristics" below.}$

4.  $E_{AS}$  of 541 mJ is based on starting  $T_J$  = 25 °C, L = 3 mH,  $I_{AS}$  = 19 A,  $V_{DD}$  = 30 V,  $V_{GS}$  = 10 V. 100% test at L = 1 mH,  $I_{AS}$  = 25 A.





## Typical Characteristics (continued)

## SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS6699S.

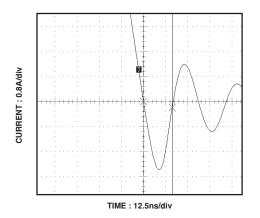


Figure 12. FDS6699S SyncFET body diode reverse recovery characteristic.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

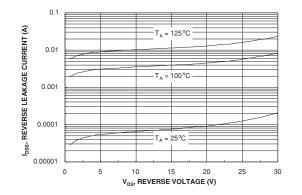


Figure 13. SyncFET body diode reverse leakage versus drain-source voltage and temperature.



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